

Dual Power Schottky Diode

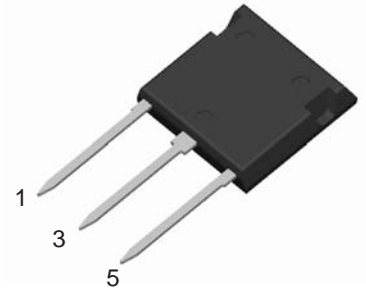
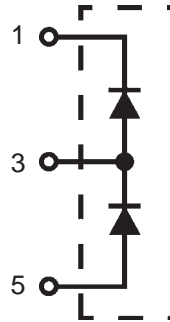
in ISOPLUS i4-PAC™

FSS 100-008A

$$V_{RRM} = 80 \text{ V}$$

$$V_F = 0.9 \text{ V}$$

$$I_{F(AV)M} = 90 \text{ A}$$



Rectifier Bridge

Symbol	Conditions	Maximum Ratings	
V_{RRM}		80	V
I_{FAV}	$T_C = 90^\circ\text{C}$; sine 180°	85	A
$I_{F(AV)M}$	$T_C = 90^\circ\text{C}$; d = 0.5 rectangular	90	A
P_{tot}	$T_C = 25^\circ\text{C}$ (per diode)	100	W

Features

- Schottky diodes
 - very low forward voltage
 - extremely fast switching
 - blocking capability optimized for elevated temperature
- ISOPLUS i4-PAC™ package
 - DCB isolated back surface
 - enlarged creepage towards heatsink
 - application friendly pinout
 - low inductive current path
 - high reliability
 - industry standard outline

Symbol	Conditions	Characteristic Values		
		(T _{VJ} = 25°C, unless otherwise specified)		
		min.	typ.	max.
V_F	$I_F = 75 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	0.9	1.0	V
		0.8		V
I_R	$V_R = V_{RRM}$; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	2.5	2	mA mA
R_{thJC}	(per diode)		1.4	K/W

Applications

- for use in
 - automotive drives and converters
 - hand held tools
 - low voltage power supplies
 - battery chargers
 - solar converters
- operating
 - as free wheeling diode of choppers for supply of motors or transformers
 - as high frequency secondary rectifier
 - anti paralleled to MOSFETs complementing their intrinsic body diode

Component

Symbol	Conditions	Maximum Ratings	
T_{VJ}		-55...+175	°C
T_{stg}		-55...+125	°C
V_{ISOL}	$I_{ISOL} \leq 1 \text{ mA}; 50/60 \text{ Hz}$	2500	V~
F_c	mounting force with clip	20...120	N

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
C_p	coupling capacity between shorted pins and mounting tab in the case		40	pF
d_s, d_A	pin - pin	5.5		mm
d_s, d_A	pin - backside metal	5.5		mm
R_{thCH}	with heatsink compound		0.15	K/W
Weight			9	g

Dimensions in mm (1 mm = 0.0394")
